# MMBV109LT1, MV209

**Preferred Devices** 

# **Silicon Epicap Diodes**

Designed for general frequency control and tuning applications; providing solid-state reliability in replacement of mechanical tuning methods.

## Features

- High Q with Guaranteed Minimum Values at VHF Frequencies
- Controlled and Uniform Tuning Ratio
- Available in Surface Mount Package
- Pb–Free Packages are Available

## MAXIMUM RATINGS (T<sub>C</sub> = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Reverse Voltage	V <sub>R</sub>	30	Vdc
Forward Current	١ <sub>F</sub>	200	mAdc
Forward Power Dissipation MMBV109LT1 @ T <sub>A</sub> = 25°C Derate above 25°C @ T <sub>A</sub> = 25°C Derate above 25°C	PD	200 2.0 200 1.6	mW mW/°C mW mW/°C
Junction Temperature	TJ	+125	°C
Storage Temperature Range	T <sub>stg</sub>	-55 to +150	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

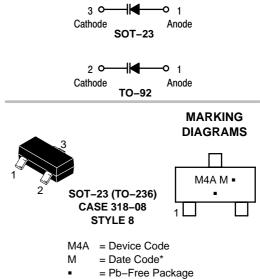
Characteristic	Symbol	Min	Тур	Max	Unit
Reverse Breakdown Voltage ( $I_R = 10 \ \mu Adc$ )	V <sub>(BR)R</sub>	30	-	-	Vdc
Reverse Voltage Leakage Current ( $V_R = 25 \text{ Vdc}$ )	I <sub>R</sub>	-	-	0.1	μAdc
Diode Capacitance Temperature Coefficient ( $V_R = 3.0 \text{ Vdc}, f = 1.0 \text{ MHz}$ )	TC <sub>C</sub>	-	300	-	ppm/°C



# **ON Semiconductor®**

http://onsemi.com

# 26–32 pF VOLTAGE VARIABLE CAPACITANCE DIODES



(Note: Microdot may be in either location) \*Date Code orientation and/or overbar may vary depending upon manufacturing location.



## ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

**Preferred** devices are recommended choices for future use and best overall value.

# MMBV109LT1, MV209

			C <sub>t</sub> , Diode Capacitance V <sub>R</sub> = 3.0 Vdc, f = 1.0 MHz pF			Q, Figure of Merit $V_R = 3.0 \text{ Vdc}$ f = 50 MHz	C <sub>R</sub> , Capacitance Ratio C <sub>3</sub> /C <sub>25</sub> f = 1.0 MHz (Note 1)	
Device	Package	Shipping <sup>†</sup>	Min	Nom	Мах	Min	Min	Max
MMBV109LT1	SOT-23	3,000 / Tape & Reel						
MMBV109LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel						
MMBV109LT3	SOT-23	10,000 / Tape & Reel						
MMBV109LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel	26	29	32	200	5.0	6.5
MV209	TO-92	1,000 Units / Bag						
MV209G	TO-92 (Pb-Free)	1,000 Units / Bag						

1.  $C_R$  is the ratio of  $C_t$  measured at 3 Vdc divided by  $C_t$  measured at 25 Vdc.

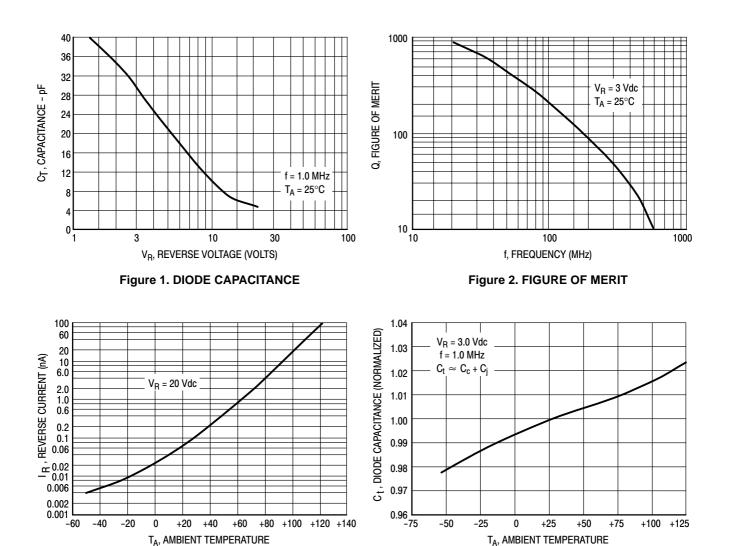


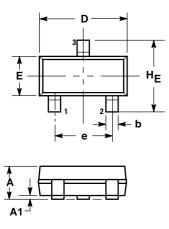


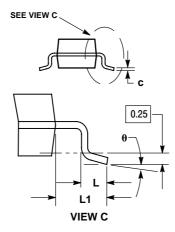
Figure 4. DIODE CAPACITANCE

#### NOTES ON TESTING AND SPECIFICATIONS

# PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 **ISSUE AN** 



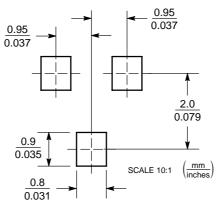


- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
  4. 318–01 THRU –07 AND –09 OBSOLETE, NEW STANDARD 318–08.

	MILLIMETERS			INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.89	1.00	1.11	0.035	0.040	0.044	
A1	0.01	0.06	0.10	0.001	0.002	0.004	
b	0.37	0.44	0.50	0.015	0.018	0.020	
С	0.09	0.13	0.18	0.003	0.005	0.007	
D	2.80	2.90	3.04	0.110	0.114	0.120	
E	1.20	1.30	1.40	0.047	0.051	0.055	
е	1.78	1.90	2.04	0.070	0.075	0.081	
L	0.10	0.20	0.30	0.004	0.008	0.012	
L1	0.35	0.54	0.69	0.014	0.021	0.029	
HE	2.10	2.40	2.64	0.083	0.094	0.104	

STYLE 8:

**SOLDERING FOOTPRINT\*** 



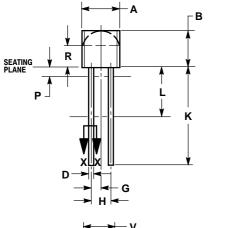
\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

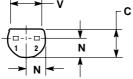
PIN 1.

ANODE NO CONNECTION CATHODE 2. 3.

### PACKAGE DIMENSIONS

TO-92 (TO-226AC) CASE 182-06 ISSUE L









- NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.
- 3. CONTOUR OF PACKAGE BEYOND ZONE R IS UNCONTROLLED.
- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIMETER		
DIM	MIN	MAX	MIN	MAX	
Α	0.175	0.205	4.45	5.21	
В	0.170	0.210	4.32	5.33	
С	0.125	0.165	3.18	4.19	
D	0.016	0.021	0.407	0.533	
G	0.050 BSC		1.27 BSC		
Н	0.100 BSC		2.54 BSC		
J	0.014	0.016	0.36	0.41	
Κ	0.500		12.70		
L	0.250		6.35		
Ν	0.080	0.105	2.03	2.66	
Ρ		0.050		1.27	
R	0.115		2.93		
٧	0.135		3.43		

PIN 1 ANODE

2. CATHODE

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